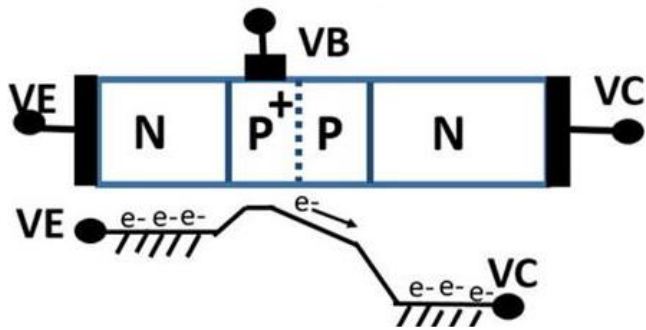


Invention and Historical Development Efforts of Pinned Buried Photodiode.

JPA1975-127646, JPA1975-127647 and JPA1975-134986 are the evidence that Yoshiaki Hagiwara at Sony is the inventor of Pinned Buried Photodiode and the SSDM1978 paper by Hagiwara team in Sony is the evidence that Hagiwara developed the first Pinned Buried Photodiode with the no-image-lag feature, the low surface dark current and the excellent short-wave blue-light sensitivity.

Drift Field Transistor



Herbert Kroemer, 1953

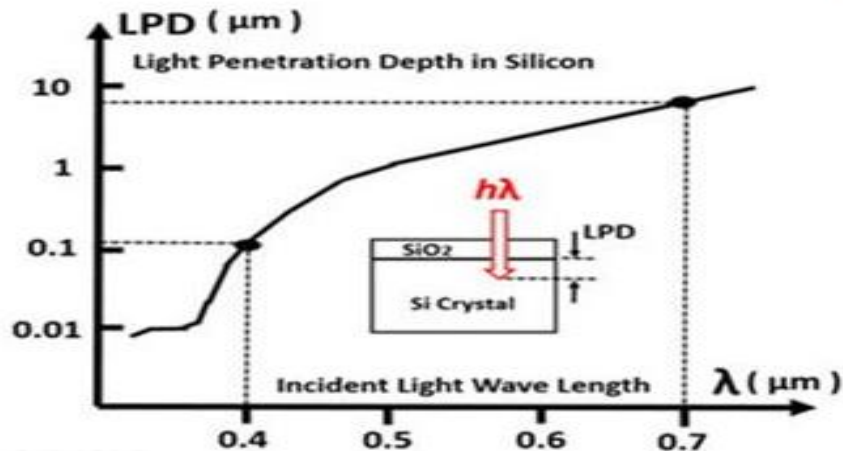
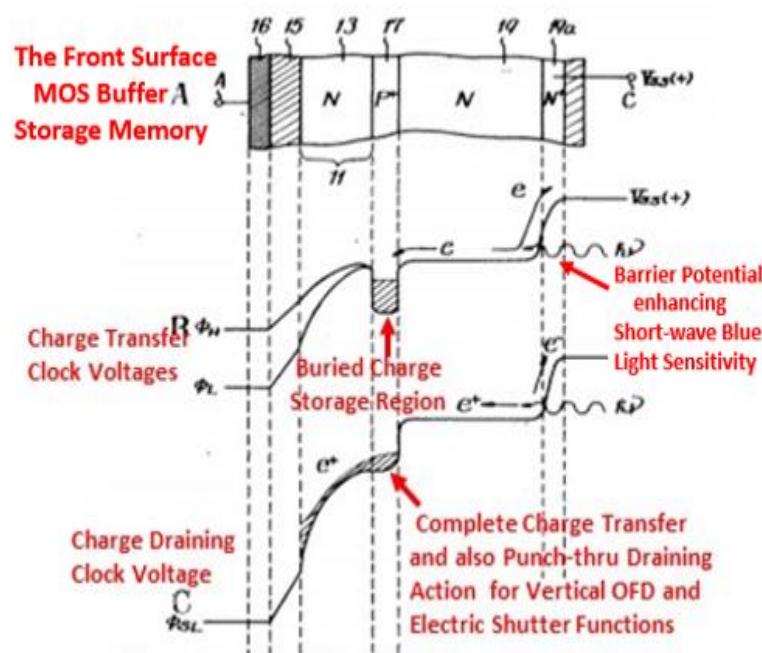


Fig. 7 第 7 图



JPA1975-127647 with Global Shutter Function

JPA1975-127647

N+NP+N Double Junction Dynamic Photo Transistor type Pinned Surface Buried Storage Photodiode

No Image Lag Problem

No Surface Dark Current Noise

Excellent Short-Wave Light Sensitivity